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# 2SK2795

Silicon N Channel MOS FET  
UHF Power Amplifier

# HITACHI

ADE-208-466 A (Z)  
2nd. Edition  
November. 1996

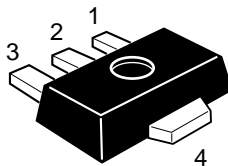
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## Features

- High power output, High gain, High efficiency  
PG = 11dB, Pout = 24dBm,  $\eta_D = 40\% \text{ min.}$  (f = 836.5MHz)
- Compact package capable of surface mounting

## Outline

UPAK



1. Gate
2. Source
3. Drain
4. Source

This Device is sensitive to Electro Static Discharge.  
An Adequate handling procedure is requested.

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## 2SK2795

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### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	VDSS	10	V
Gate to source voltage	VGSS	±6	V
Drain current	ID	0.17	A
Drain peak current	ID(pulse)*1	0.3	A
Channel dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-45 to +150	°C

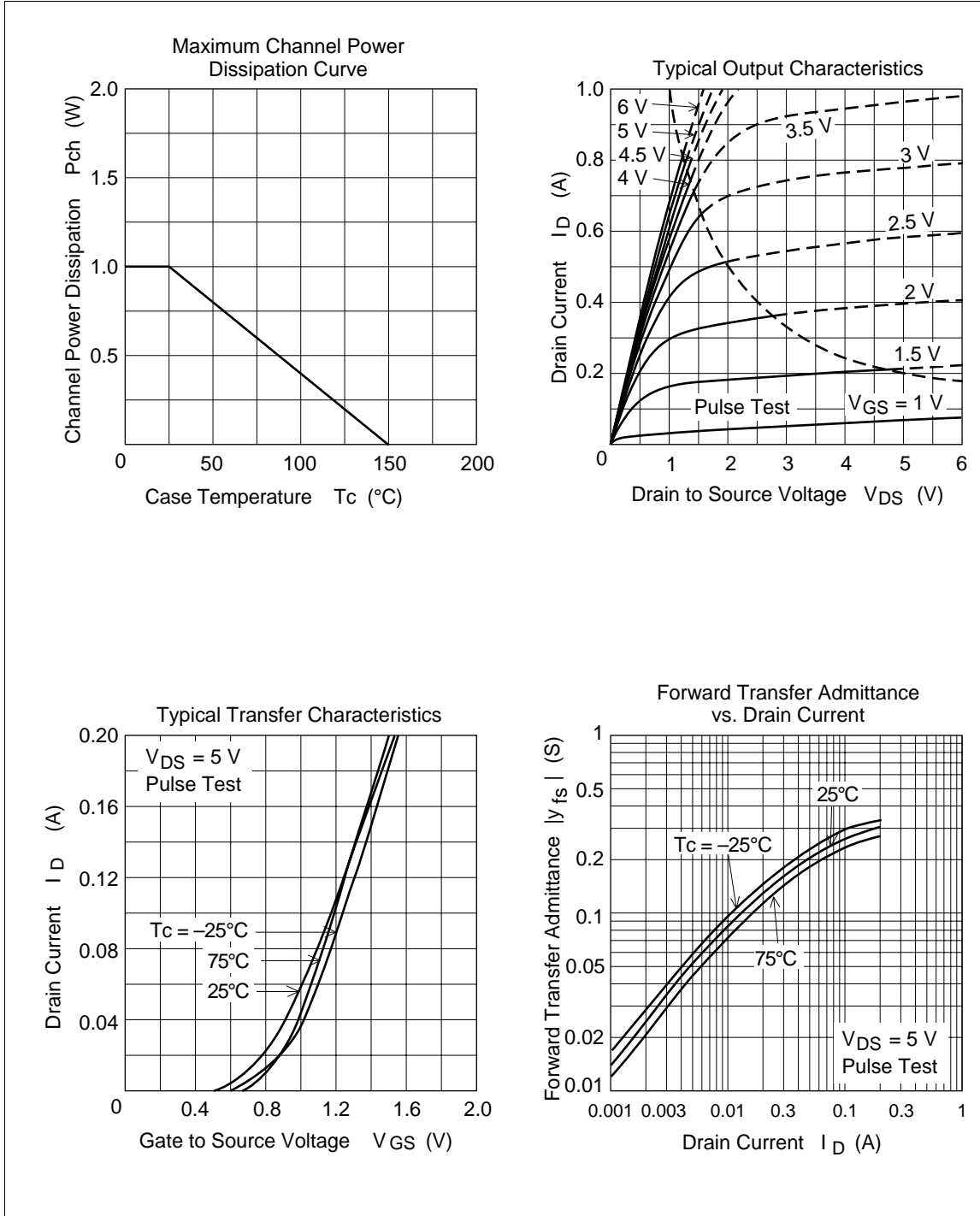
Note: 1.  $PW \leq 10ms$ , duty cycle  $\leq 50\%$   
2. Value at  $Tc = 25^\circ C$

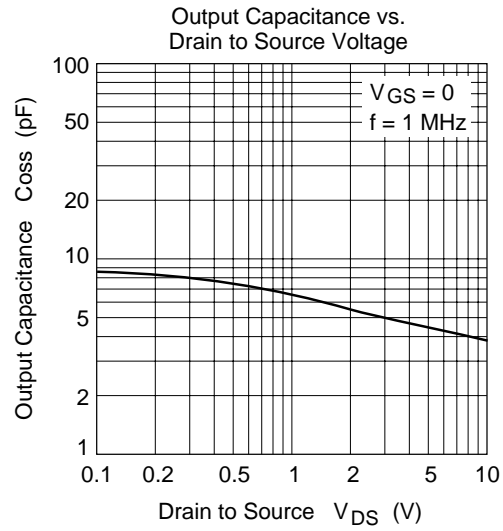
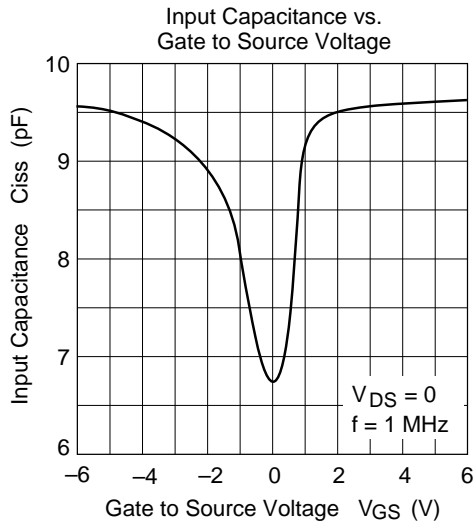
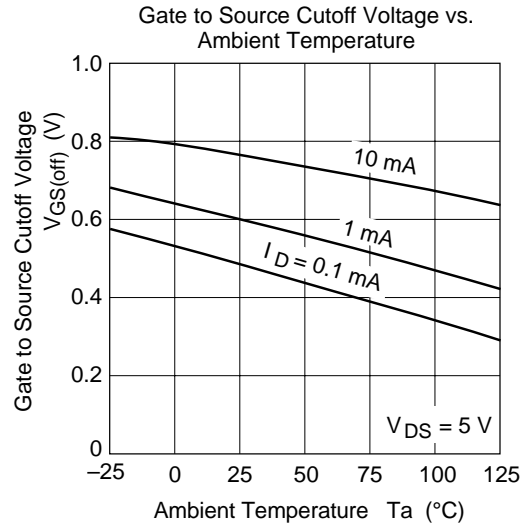
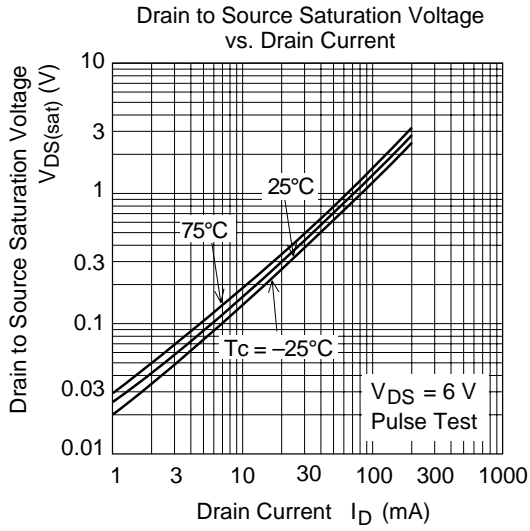
### Electrical Characteristics (Ta = 25°C)

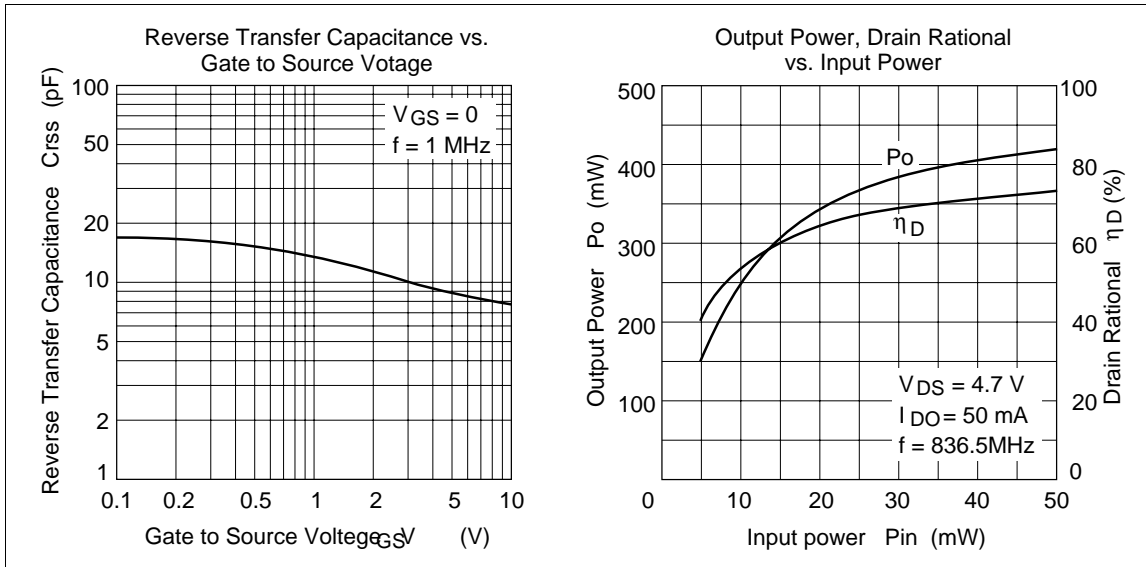
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero gate voltage drain current	IDSS	—	—	10	μA	VDS = 10 V, VGS = 0
Gate to source leak current	IGSS	—	—	±5.0	μA	VGS = ±6V, VDS = 0
Gate to source cutoff voltage	VGS(off)	0.3	—	1.0	V	ID = 1mA, VDS = 5V
Input capacitance	Ciss	—	9.5	—	pF	VGS = 2V, VDS = 0 f = 1MHz
Output capacitance	Coss	—	4.5	—	pF	VDS = 5, VGS = 0 f = 1MHz
Output Power	Pout	24	—	—	dBm	VDS = 4.7V f = 836.5MHz Pin = 13dBm
Drain Rational	ηD	40	—	—	%	VDS = 4.7V f = 836.5MHz Pin = 13dBm

Note: 3. Marking is "DX".

Main Characteristics







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## Package Dimensions

Unit: mm

